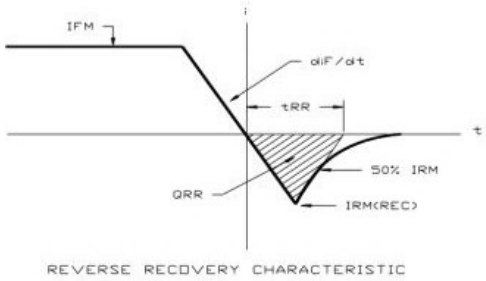
Features

1) Full diffusion structure
2) High current density
3) Very low on state pressure drop
4) Sealed ceramic tube shell packaging
5) Ultra low thermal resistance



REVERSE RECOVERY CHARACTERISTIC

Reverse blocking

Device model	V_{RRM} (1)	V_{RSM} (2)
13500/02	200V	300V
13500/04	400V	450V

V_{RRM} = Repetitive peak reverse voltage

Repetitive peak current	I_{RRM}	10Ma 75 mA (3)

Main parameter

CHARACTERISTIC	SYMBOL	MINIMUM VALUE	MAXIMUM VALUE	TYPICAL VALUE	UNIT	TEST CONDITIONS
Mean on-state current	$I_{F(AV)}$		13500		A	SINE,T_c =85℃
Root Mean Square	$I_{F(RMS)}$		21200		A	
Surge on-state current	I_{FSM}		85000		A	10ms half sine wave，VR=0V, T_j = 180℃
I^2t for fusing coordination	I^2t		36100		KA^2s	10ms half sine wave，VR=0V,T_J = 180℃
Peak on-state voltage	V_{FM}		1.01		V	I_{FM} =6000 A; 25 °C
Threshold voltage	V_{TO}		0.76		V	T_j = 180 °C
On-state slope resistance	r_T		0.021		mΩ	T_j = 180 °C
Reverse recovery current	$I_{RM(REC)}$				A	I_{FM} = 1000 A; dI_F/dt = 10 A/μs;Tjmax
Reverse recovery of charge	Q_{rr}				μC	I_{FM} = 1000 A; dI_F/dt = 10 A/μs;Tjmax
Reverse recovery time	t_{RR}				μs	

CHARACTERISTIC	SYMBOL	MINIMUM	MAXIMUM	TYPICAL	UNIT	TEST CONDITIONS
	T_j	-40	+180		°C	
Stored temperature	T_{stg}	-40	+180		°C	
Thermal resistance Junction to case	$R_{\Theta(j-c)}$		0.0039		°C/W	double side cooled
Thermal resistance case to heatsink	$R_{\Theta(j-c)}$		0.026		°C/W	single side cooled
Creepage distance	D_S		2		mm	
Air breakdown distance	Da		2		mm	
Installation pressure	F	35	40		kN	
Weight	W			140	g	

Outline